

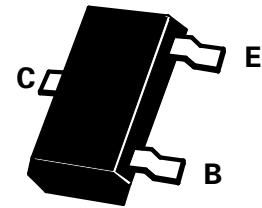
SOT23 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

ISSUE 2 – SEPTEMBER 95

BSS63

COMPLIMENTARY TYPE — BSS64

PARTMARKING DETAIL — BSS63 - T3
BSS63R - T6



ABSOLUTE MAXIMUM RATINGS.

| PARAMETER | SYMBOL | VALUE | UNIT |
|--|---------------|-------------|-------------|
| Collector-Base Voltage | V_{CBO} | -110 | V |
| Collector-Emitter Voltage | V_{CEO} | -100 | V |
| Emitter-Base Voltage | V_{EBO} | -6 | V |
| Continuous Collector Current | I_C | -100 | mA |
| Power Dissipation at $T_{amb}=25^{\circ}C$ | P_{TOT} | 330 | mW |
| Operating and Storage Temperature Range | $t_j:t_{stg}$ | -55 to +150 | $^{\circ}C$ |

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

| PARAMETER | SYMBOL | MIN. | MAX. | UNIT | CONDITIONS. |
|--------------------------------------|---------------|----------|-------------|---------------|--|
| Collector-Base Breakdown Voltage | $V_{(BR)}$ | -110 | | V | $I_C = -10\mu A$ |
| Collector-Emitter Breakdown Voltage | $V_{(BR)CEO}$ | -100 | | V | $I_C = -100\mu A^*$ |
| Emitter-Base Breakdown Voltage | $V_{(BR)EBO}$ | -6 | | V | $I_E = -10\mu A$ |
| Collector Cut-Off Current | I_{EBO} | | -100 -50 | nA μA | $V_{CB} = -90V$, $V_{CB} = -90V, T_{amb} = 150^{\circ}C$ |
| Emitter Cut-Off Current | I_{EBO} | | -200 | nA | $V_{EB} = -6V$ |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | | -250 | mV | $I_C = -25mA, I_B = -2.5mA$ |
| Base-Emitter Saturation Voltage | $V_{BE(sat)}$ | | -900 | mV | $I_C = -25mA, I_B = -2.5mA$ |
| Static Forward Current | h_{FE} | 30 30 | | | $I_C = -10mA, V_{CE} = -1V$ $I_C = 25mA, V_{CE} = 1V$ |
| Transition Frequency | f_T | 50 | Typ 85 | MHz | $V_{CE} = -5V, I_C = 25mA$ $f = 35 MHz$ |
| Output Capacitance | C_{obo} | | Typ. 3 | pF | $V_{CB} = -10V, f = 1MHz$ |

* Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$